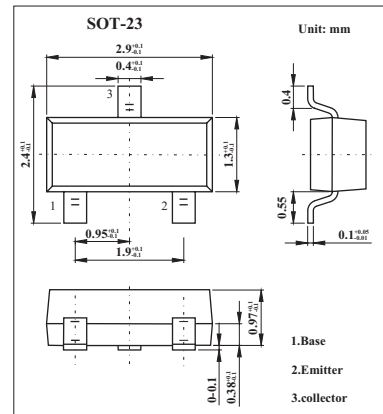


BCX70 series

■ Features

- Low current (max. 100 mA).
- Low voltage (max. 45 V).



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	45	V
Collector-emitter voltage	V _{CE0}	45	V
Emitter-base voltage	V _{EB0}	5	V
Collector current	I _c	100	mA
Peak collector current	I _{CM}	200	mA
Peak base current	I _{BM}	200	mA
Collector dissipation	P _C	250	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-65 to +150	°C
Operating ambient temperature	T _{amb}	-65 to +150	°C
Thermal resistance from junction to ambient *	R _{th(j-a)}	500	K/W

* Transistor mounted on an FR4 printed-circuit board.

BCX70 series

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit		
Collector cutoff current	ICBO	IE = 0; VCB = 45 V			20	nA		
	ICBO	IE = 0; VCB = 45 V; Tj = 150 °C			20	µA		
Emitter cutoff current	IEBO	IC = 0; VEB = 4 V			20	nA		
	BCX70G	hFE IC = 10 µA; VCE = 5 V						
	BCX70H						40	
	BCX70J						30	
	BCX70K						100	
DC current gain	BCX70G	hFE IC = 2 mA; VCE = 5 V						
	BCX70H						120	220
	BCX70J						180	310
	BCX70K						250	460
DC current gain	BCX70G	hFE IC = 50 mA; VCE = 1 V						
	BCX70H						380	630
	BCX70J						50	
	BCX70K						70	
Collector-emitter saturation voltage	VCE(sat)	IC = 10 mA; IB = 0.25 mA	50		350	mV		
		IC = 50mA; IB = 1.25 mA	100		550	mV		
Base to emitter saturation voltage	VBE(sat)	IC = 10 mA; IB = 0.25 mA	600		850	mV		
		IC = 50mA; IB = 1.25 mA	700		1050	mV		
Base to emitter voltage	VBE	IC = 2 mA; VCE = 5 V	550	650	750	mV		
Collector capacitance	Cc	IE = ie = 0; VCB = 10 V; f = 1 MHz		1.7		pF		
Emitter capacitance	Ce	IC = ic = 0; VEB = 0.5 V; f = 1 MHz		11		pF		
Transition frequency *	fT	IC = 10 mA; VCE = 5 V; f = 100 MHz	100	250		MHz		
Noise figure	NF	IC = 200 µA; VCE = 5 V; Rs = 2 kΩ; f = 1 kHz; B = 200 Hz		2	6	dB		

* Pulse test: tp ≤ 300 µs; d ≤ 0.02.

■ hFE Classification

Type Number	BCX70G	BCX70H	BCX70J	BCX70K
Marking	AG	AH	AJ	AK